

Amendments to the Claims:

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A process system comprising:
 - a chamber;
 - a supply plate which has a plurality of gas holes and supplies a process gas into said chamber through said gas holes;
 - a first diffusion portion which diffuses said gas in a direction approximately parallel to a major surface of said supply plate; and
 - a second diffusion portion which leads said gas diffused by said first diffusion portion to said gas holes, said second diffusion portion comprised of a disk-like member having a groove formed in one side thereof, said groove having through holes formed therein, wherein said second diffusion portion is placed over said supply plate to form a hollow portion between said disk-like member and said supply plate such that said gas can be supplied from said first diffusion portion to said hollow portion; and
- said process system further comprising a partition member in said hollow portion which separates said hollow portion into a center area and an end area, and a gas supply portion comprising mutually independent gas flow passages, wherein ~~at least one~~ a first gas flow passage supplies said gas via through holes

to said center area, and ~~at least one a second~~ gas flow passage supplie[[d]]s said gas via through holes to said end area, wherein the gas flow rates in the mutually independent gas flow passages are independently controlled and first and second gas flow passages are separate.

2. (Original) The process system according to claim 1, wherein said first diffusion portion is comprised of a disk like member having a plurality of grooves formed in one side thereof and communicating with one another and through holes formed in said plurality of grooves and led to the other side.

3. (Previously Presented) The process system according to claim 2, wherein at least one of said grooves in said first diffusion portion are provided at positions to which said gas is supplied, and said gas supplied to said at least one groove is dispersed to the other grooves in said first diffusion portion and flows out to the other side through said through holes respectively provided in said other grooves.

4. (Canceled)

5. (Previously Presented) The process system according to claim 2, wherein said disk-like member constituting said second diffusion portion is made of a same member as said disk-like member constituting said first diffusion

portion, and said groove constituting said second diffusion portion and said grooves constituting said first diffusion portion are formed in opposite sides of said member.

6. (Canceled)

7. (Original) The process system according to claim 1, wherein said first diffusion portion is comprised of a cylindrical member having a plurality of linear holes communicating with one another, formed by boring and sealing end portions of bored portions, at least one of said holes is supplied with said gas and said gas supplied to said at least one hole is dispersed to the other holes.

8. (Previously Presented) The process system according to claim 7, wherein said cylindrical member has connection holes provided in such a way as to be in communication with said linear holes from its one side, and said gas supplied to said linear holes is supplied to said second diffusion portion from said connection holes.

9. (Withdrawn) A process method which uses a process system comprising a chamber and a supply plate which has a plurality of gas holes and supplies a process gas into said chamber through said gas holes, comprising: a first diffusion step which linearly diffuses said gas in a direction approximately

horizontal to a major surface of said supply plate; and a second diffusion step which leads said gas diffused in said first diffusion step to said gas holes.

10. (Previously Presented) The process system according to claim 1, wherein a linear gas flow passage approximately parallel to a major surface of said supply plate is formed in said first diffusion portion, and said gas is diffused in a direction approximately parallel to the major surface of said supply plate.

11. (Previously Presented) The process system according to claim 7, wherein said first diffusion portion has a plurality of cylindrical members, and each cylindrical member comprises said plurality of linear holes formed from a sidewall of said cylindrical members toward a center thereof.

12. (Previously Presented) The process system according to claim 11, wherein said cylindrical members respectively constitute gas flow passages independent from each other.

13. (Withdrawn) A process system comprising: a chamber, a support which is provided inside said chamber for placing a process target thereon; a first gas supply passage which has gas holes, and supplies a gas through said gas holes to a position corresponding to a center area of said process target in said chamber; a second gas supply passage which has gas holes, and supplies a gas

through said gas holes to a position corresponding to an end area of said process target in said chamber; and a controller which controls a ratio of amounts of gases flowing through said first gas supply passage and said second gas supply passage.

14. (Withdrawn) The process system according to claim 13, wherein said first and second gas supply passages supply a same gas to said chamber.

15. (Withdrawn) The process system according to claim 13, wherein said controller includes a first mass flow controller provided to said first gas supply passage, a second mass flow controller provided to said second gas supply passage, and a control unit which controls said first and second mass flow controllers.

16. (Withdrawn) The process system according to claim 13, wherein said controller controls amounts of gases output from said first and second gas supply passages in such a way as to make a thickness of a film formed on said process target uniform.

17. (Withdrawn) The process system according to claim 13, wherein said controller controls kinds and amounts of gases output from said first and second

gas supply passages in such a way as to make thicknesses of a plurality of films formed on said process target uniform respectively.

18. (Withdrawn) The process system according to claim 13, wherein said first and second gas supply passages have, in common, a supply plate which has a plurality of gas holes for supplying a process gas into said chamber through said gas holes; and said first and second gas supply passages respectively have a first diffusion portion which diffuses said gas in a direction approximately horizontal to a major surface of said supply plate, and a second diffusion portion which leads said gas diffused by said first diffusion portion to said gas holes.

19. (Withdrawn) A process method comprising: setting a process target inside a chamber; and performing a film forming process by supplying process gases with different rates to a position corresponding to a center area of said process target in said chamber and to a position corresponding to an end area of said process target.

20. (Previously Presented) The process system according to claim 1, wherein each mutually independent gas flow passage is adapted to receive said process gas from a common gas supply source.

21. (Currently Amended) A process system comprising:

a chamber;

a supply plate which has a plurality of gas holes and supplies a process gas into said chamber through said gas holes;

a first diffusion portion which diffuses said gas in a direction approximately parallel to a major surface of said supply plate; and

a second diffusion portion which leads said gas diffused by said first diffusion portion to said gas holes,

wherein said first diffusion portion and said second diffusion portion comprise mutually independent gas flow passages, wherein ~~at least one a first~~ gas flow passage supplies said process gas only into a center area of said chamber, and ~~at least one a second~~ gas flow passage supplies said process gas only into an end area of said chamber, wherein the process gas in ~~a the~~ first independent gas flow passage and the process gas in ~~a the~~ second independent gas flow passage do not mix before flowing into said chamber.

22. (Previously Presented) The process system according to claim 21, wherein the process gas flow rates in the mutually independent gas flow passages are independently controlled.

23. (New) The process system according to claim 1, wherein the gas flow rates into the chamber are independently controlled.